Silicon Bidirectional Triode Thyristors

... designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO-92 package which is readily adaptable for use in automatic insertion equipment.

- One-Piece, Injection-Molded Unibloc Package
- Sensitive Gate Triggering in Four Trigger Modes for all possible Combinations of Trigger Sources, and Especially for Circuits that Source Gate Drives
- All Diffused and Glassivated Junctions for Maximum Uniformity of Parameters and Reliability

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Gate Open, T _J = -40 to +110°C)(1) 1/2 Sine Wave 50 to 60 Hz, Gate Open	V _{DRM}		Volts	
MAC97A4 MAC97A6 MAC97–8, MAC97A8		200 400 600		
On-State RMS Current Full Cycle Sine Wave 50 to 60 Hz (T _C = +50°C)	IT(RMS	0.8	Amp	
Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, T _A = 110°C)	ITSM	8.0	Amps	
Circuit Fusing Considerations $T_J = -40$ to +110°C (t = 8.3 ms)	l ² t	0.26	A ² s	
Peak Gate Voltage (t ≤ 2.0 μs)	V _{GM}	5.0	Volts	
Peak Gate Power (t ≤ 2.0 μs)	P _{GM}	5.0	Watts	
Average Gate Power ($T_C = 80^{\circ}C$, $t \le 8.3 \text{ ms}$)	ms) P _{G(AV)} 0.1		Watt	
Peak Gate Current (t ≤ 2.0 μs)	≤ 2.0 μs) I _{GM}		Amp	
Operating Junction Temperature Range	TJ	-40 to +110	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	

THERMAL CHARACTERISTICS

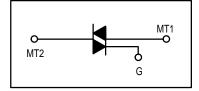
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	75	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W

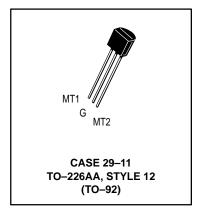
⁽¹⁾ V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

MAC97,A IMPROVED SERIES

Motorola preferred devices

TRIACs
0.8 AMPERE RMS
200 — 600 VOLTS





Preferred devices are Motorola recommended choices for future use and best overall value.

REV₃



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$, and Either Polarity of MT2 to MT1 Voltage unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current(1) (V _D = Rated V _{DRM} , T _J = 110°C, Gate Open)	^I RRM	<u> </u>	_	0.1	mA
Peak On-State Voltage (Either Direction) (I _{TM} = 1.1 A Peak; Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2.0%)	VTM	_	_	1.65	Volts
Gate Trigger Current (Continuous dc) (V _D = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) MT2(+), G(+) MT2(+), G(-)	^I GT	_ _ _ _	- - - -	10 10 10 10 5.0	mA
MT2(-), G(-) MT2(-), G(+) MAC97A		_	_	5.0 7.0	
Gate Trigger Voltage, (Continuous dc) $ (V_D=12\ Vdc,\ R_L=100\ Ohms) $ $ MT2(+),\ G(+)\ All\ Types $ $ MT2(+),\ G(-)\ All\ Types $ $ MT2(-),\ G(-)\ All\ Types $ $ MT2(-),\ G(+)\ All\ Types $ $ (V_D=Rated\ V_{DRM},\ R_L=10\ k\ Ohms,\ T_J=110^\circ C) $ $ MT2(+),\ G(+);\ MT2(-),\ G(-);\ MT2(+),\ G(-)\ All\ Types $ $ MT2(-),\ G(+)\ All\ Types $	VGT			2.0 2.0 2.0 2.5 —	Volts
Holding Current $(V_D = 12 \text{ Vdc}, I_{TM} = 200 \text{ mA}, \text{ Gate Open})$	lН	_	_	5.0	mA
Gate Controlled Turn–On Time $(V_D = Rated V_{DRM}, I_{TM} = 1.0 A pk, I_G = 25 mA)$	tgt		2.0	_	μs
Critical Rate–of–Rise of Commutation Voltage (f = 250 Hz, I_{TM} = 1.0 A, Commutating di/dt = 1.5 A/mS, On–State Current Duration = 2.0 mS, V_{DRM} = 200 V, Gate Unenergized, T_{C} = 110°C, Gate Source Resistance = 150 Ω , See Figure 13)	dv/dt _C	1.5	_	_	V/µs
Critical Rate-of-Rise of Off State Voltage (V _{pk} = Rated V _{DRM} , T _C = 110°C, Gate Open, Exponential Method)	dv/dt	10	_	_	V/μs

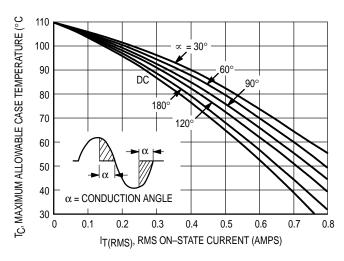


Figure 1. RMS Current Derating

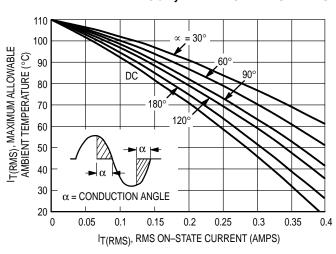


Figure 2. RMS Current Derating

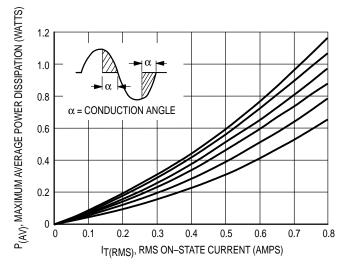


Figure 3. Power Dissipation

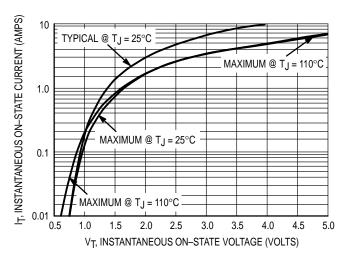


Figure 4. On-State Characteristics

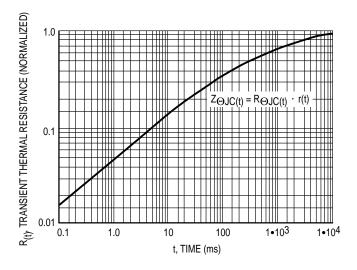


Figure 5. Transient Thermal Response

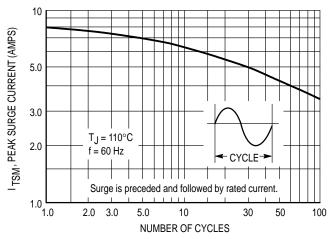


Figure 6. Maximum Allowable Surge Current

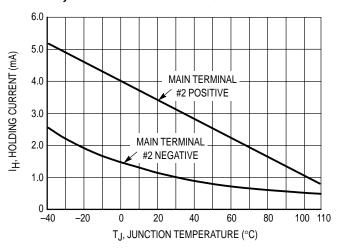


Figure 7. Typical Holding Current Variation

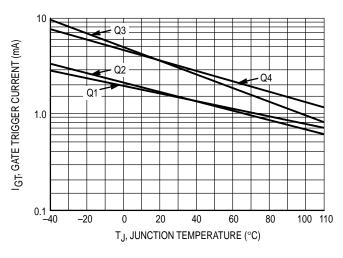


Figure 8. Typical Gate Trigger Current Variation

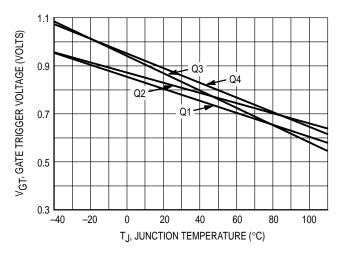


Figure 9. Gate Trigger Voltage Variation

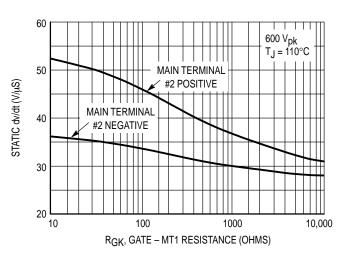


Figure 10. Exponential Static dv/dt versus

Gate – MT1 Resistance

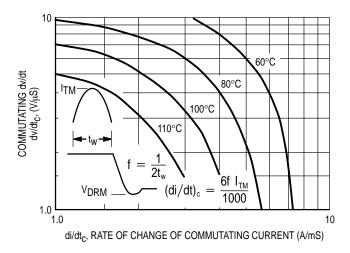


Figure 11. Typical Commutating dv/dt versus Current Crossing Rate and Junction Temperature

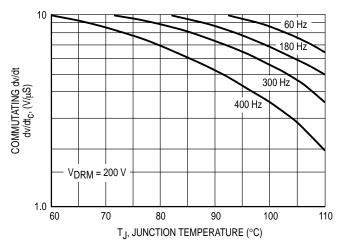
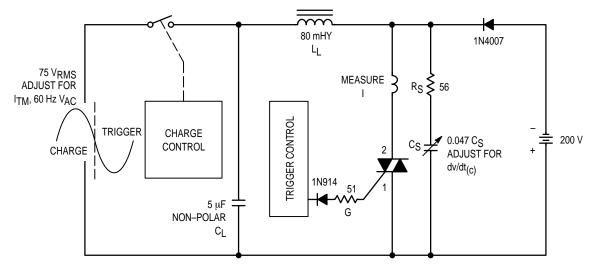


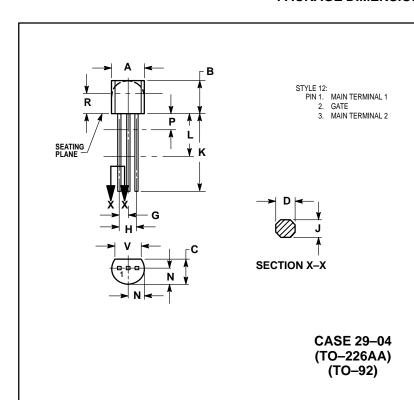
Figure 12. Typical Commutating dv/dt versus Junction Temperature at 0.8 Amps RMS



NOTE: Component values are for verification of rated $(dv/dt)_C$. See AN1048 for additional information.

Figure 13. Simplified Q₁ (dv/dt)_C Test Circuit

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93	-	
V	0.135		3.43		

NOTES

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USA/EUROPE/Locations Not Listed: Motorola Literature Distribution; P.O. Box 5405, Denver, Colorado 80217. 1–303–675–2140 or 1–800–441–2447

JAPAN: Motorola Japan Ltd.; SPD, Strategic Planning Office, 141, 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan. 81–3–5487–8488

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